

IRFR825TRPbF

HEXFET® Power MOSFET

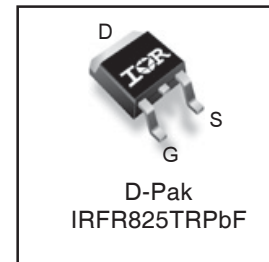
Applications

- Zero Voltage Switching SMPS
- Uninterruptible Power Supplies
- Motor Control applications

V_{DSS}	$R_{DS(on)}$ typ.	T_{rr} typ.	I_D
500V	1.05Ω	92ns	6.0A

Features and Benefits

- Fast body diode eliminates the need for external diodes in ZVS applications.
- Lower Gate charge results in simpler drive requirements.
- Higher Gate voltage threshold offers improved noise immunity.



Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	6.0	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	3.9	
I_{DM}	Pulsed Drain Current ①	24	
P_D @ $T_C = 25^\circ\text{C}$	Power Dissipation	119	W
	Linear Derating Factor	1.0	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery dv/dt ③	9.9	V/ns
T_J	Operating Junction and	-55 to + 150	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	6.0	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	24		
V_{SD}	Diode Forward Voltage	—	—	1.2	V	$T_J = 25^\circ\text{C}$, $I_S = 6.0\text{A}$, $V_{GS} = 0\text{V}$ ④
t_{rr}	Reverse Recovery Time	—	92	138	ns	$T_J = 25^\circ\text{C}$, $I_F = 6.0\text{A}$
		—	152	228		$T_J = 125^\circ\text{C}$, $di/dt = 100\text{A}/\mu\text{s}$ ④
Q_{rr}	Reverse Recovery Charge	—	167	251	nC	$T_J = 25^\circ\text{C}$, $I_S = 6.0\text{A}$, $V_{GS} = 0\text{V}$ ④
		—	292	438		$T_J = 125^\circ\text{C}$, $di/dt = 100\text{A}/\mu\text{s}$ ④
I_{RRM}	Reverse Recovery Current	—	3.6	5.4	A	$T_J = 25^\circ\text{C}$, $I_S = 6.0\text{A}$, $V_{GS} = 0\text{V}$ $di/dt = 100\text{A}/\mu\text{s}$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes ① through ⑦ are on page 2

www.irf.com

IRFR825TRPbF

International
IR Rectifier

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	500	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.33	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	1.05	1.3	Ω	$V_{GS} = 10V, I_D = 3.7A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 500V, V_{GS} = 0V$
		—	—	2.0	mA	$V_{DS} = 400V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100	nA	$V_{GS} = -20V$

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
gfs	Forward Transconductance	7.5	—	—	S	$V_{DS} = 50V, I_D = 3.7A$
Q_g	Total Gate Charge	—	—	34	nC	$I_D = 6.0A$ $V_{DS} = 400V$ $V_{GS} = 10V$, See Fig. 14a & 14b ④
Q_{gs}	Gate-to-Source Charge	—	—	11		
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	14		
$t_{d(on)}$	Turn-On Delay Time	—	8.5	—		
t_r	Rise Time	—	25	—	ns	$V_{DD} = 250V$ $I_D = 6.0A$ $R_G = 7.5\Omega$ $V_{GS} = 10V$, See Fig. 15a & 15b ④
$t_{d(off)}$	Turn-Off Delay Time	—	30	—		
t_f	Fall Time	—	20	—		
C_{iss}	Input Capacitance	—	1346	—	pF	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1.0\text{KHz}$, See Fig. 5 $V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$ $V_{GS} = 0V, V_{DS} = 400V, f = 1.0\text{MHz}$ $V_{GS} = 0V, V_{DS} = 0V$ to $400V$ ⑤
C_{oss}	Output Capacitance	—	76	—		
C_{rss}	Reverse Transfer Capacitance	—	15	—		
C_{oss}	Output Capacitance	—	1231	—		
C_{oss}	Output Capacitance	—	25	—		
$C_{oss \text{ eff.}}$	Effective Output Capacitance	—	51	—		
$C_{oss \text{ eff. (ER)}}$	Effective Output Capacitance (Energy Related)	—	43	—		

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	178	mJ
I_{AR}	Avalanche Current ①	—	3	A
E_{AR}	Repetitive Avalanche Energy ①	—	11.9	mJ

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑥	—	1.05	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ⑦	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See Fig. 11)
- ② Starting $T_J = 25^\circ\text{C}$, $L = 40\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 3.0A$. (See Figure 13).
- ③ $I_{SD} = 6.0A$, $di/dt \leq 416A/\mu s$, $V_{DD} V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$.
- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

- ⑤ $C_{oss \text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} . $C_{oss \text{ eff. (ER)}}$ is a fixed capacitance that stores the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑥ R_{θ} is measured at T_J approximately 90°C
- ⑦ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note # AN-994 techniques refer to application note #AN-994.

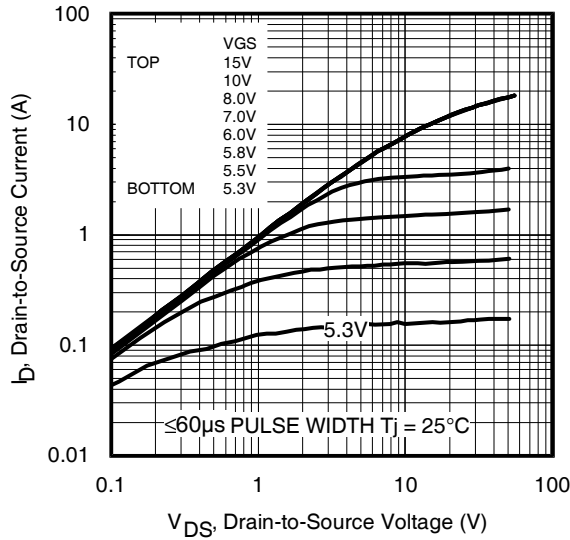


Fig 1. Typical Output Characteristics

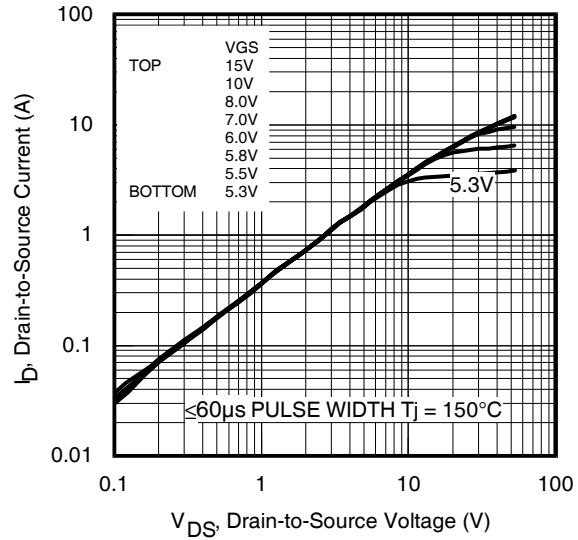


Fig 2. Typical Output Characteristics

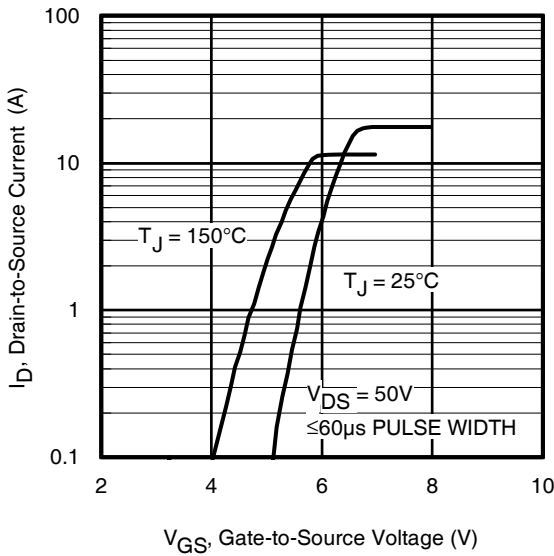


Fig 3. Typical Transfer Characteristics

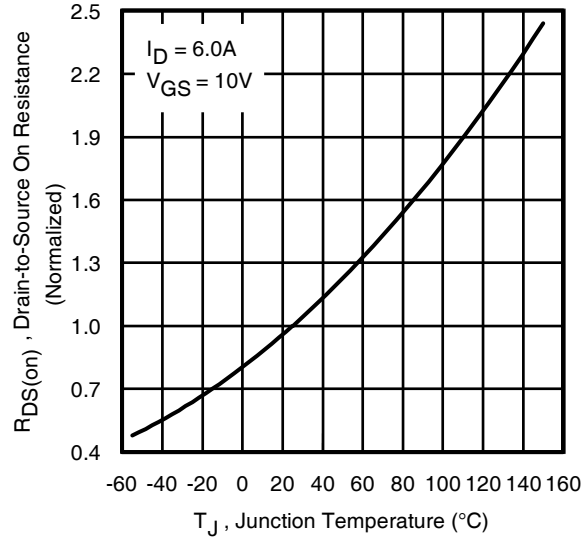


Fig 4. Normalized On-Resistance Vs. Temperature

IRFR825TRPbF

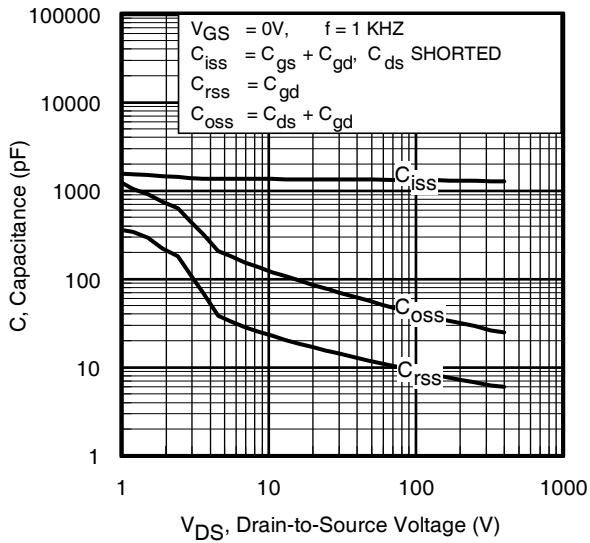


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

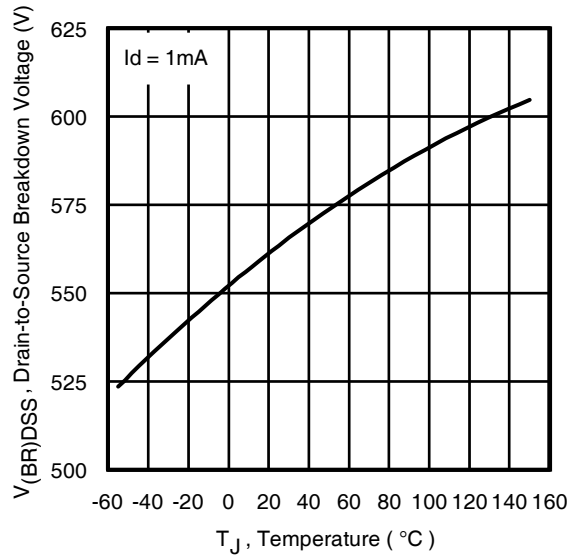
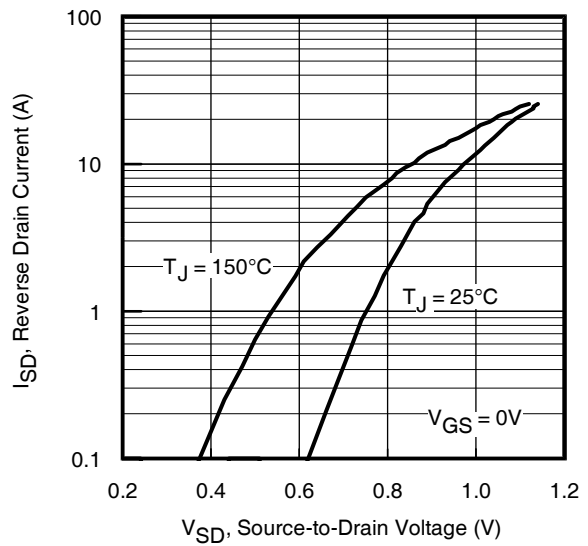
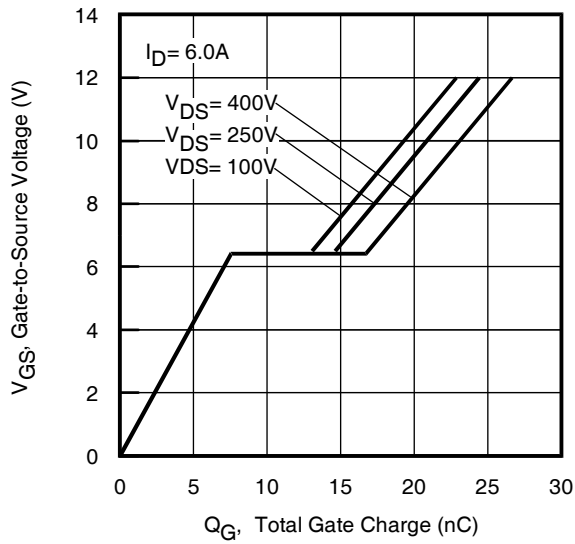


Fig 6. Typ. Breakdown Voltage vs. Temperature



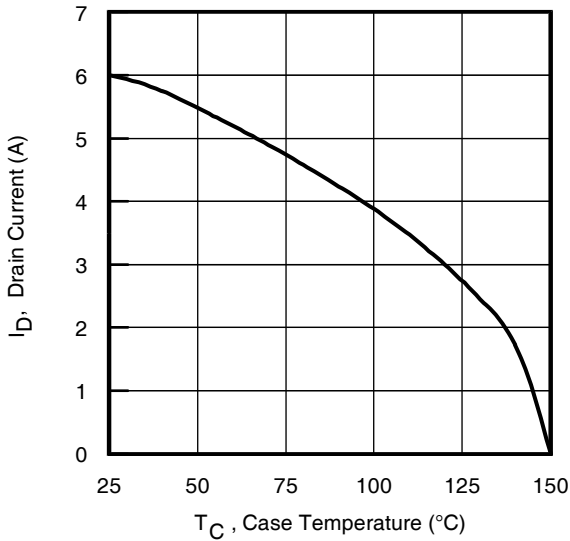


Fig 9. Maximum Drain Current Vs. Case Temperature

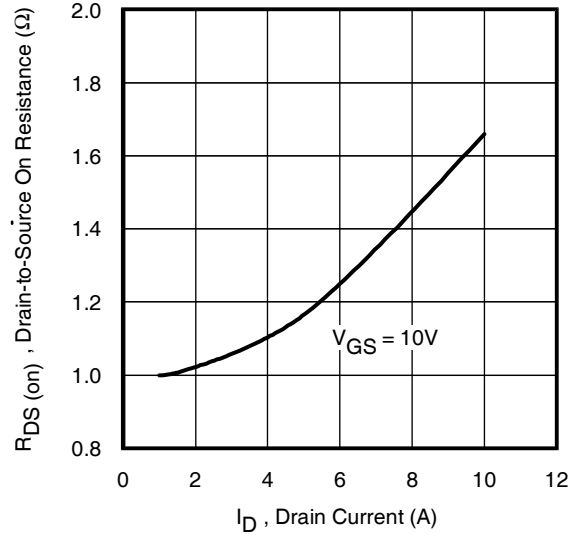


Fig 9. Typical $R_{DS(on)}$ Vs. Drain Current

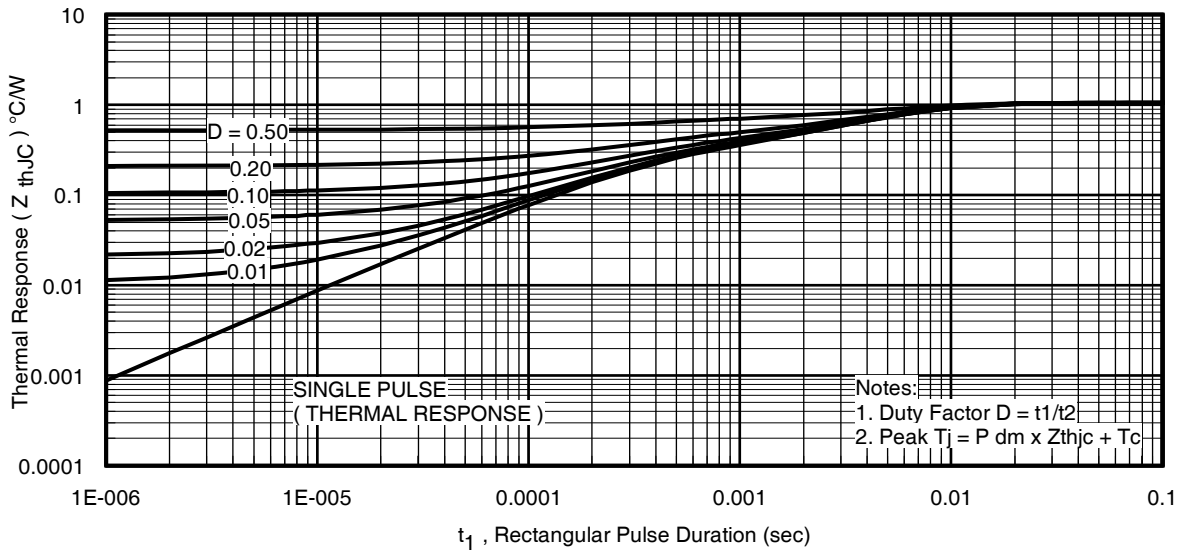


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

IRFR825TRPbF

International
IR Rectifier

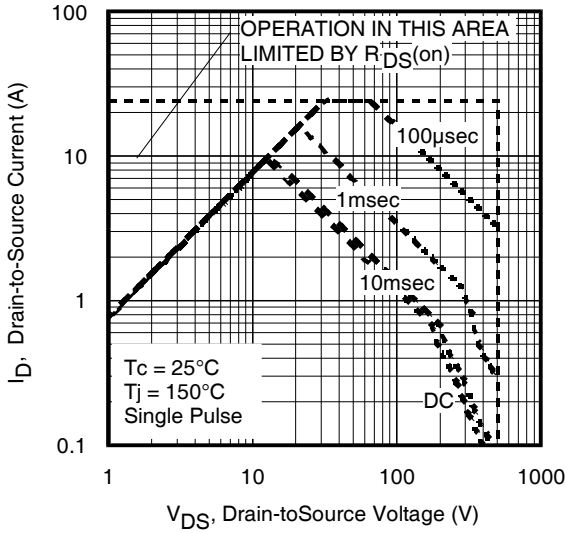


Fig 12. Maximum Safe Operating Area

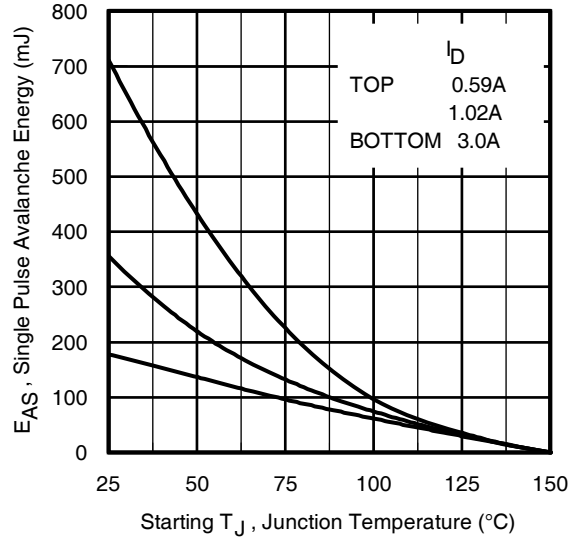


Fig 13. Maximum Avalanche Energy vs. Drain Current

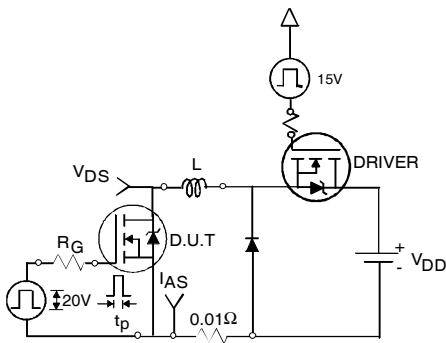


Fig 13a. Unclamped Inductive Test Circuit

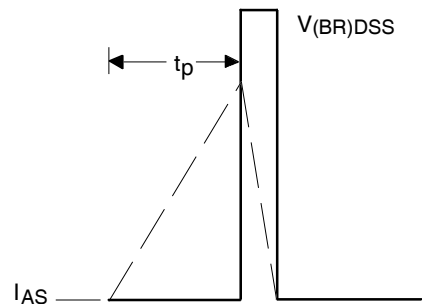


Fig 13b. Unclamped Inductive Waveforms

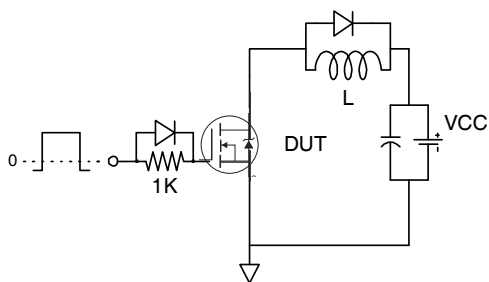


Fig 14a. Gate Charge Test Circuit

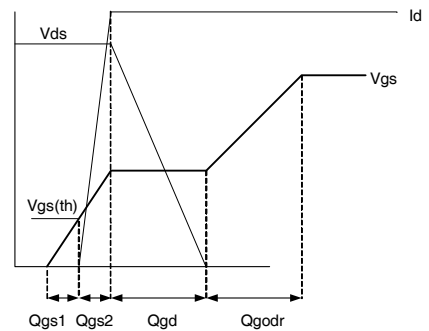


Fig 14b. Gate Charge Waveform

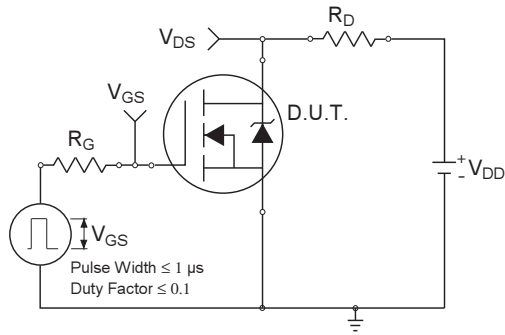


Fig 15a. Switching Time Test Circuit

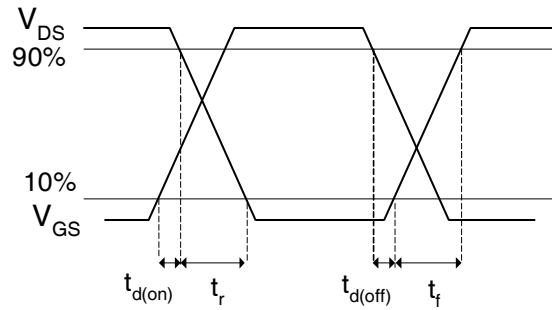
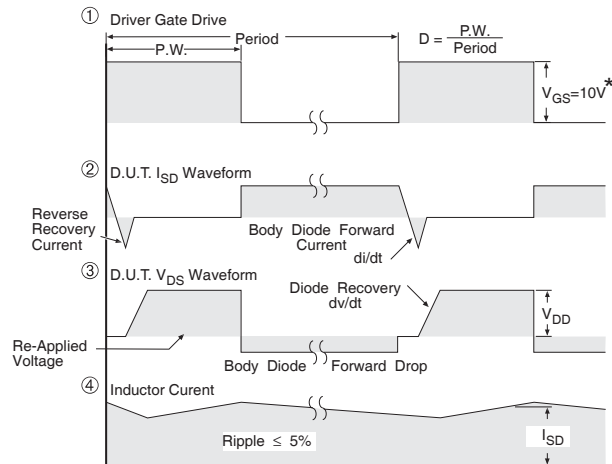
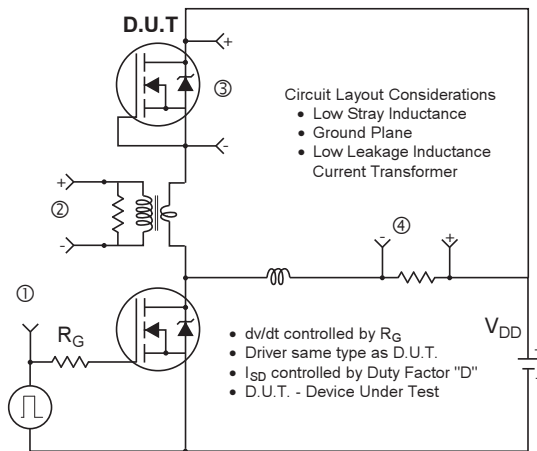


Fig 15b. Switching Time Waveforms



* $V_{GS} = 5V$ for Logic Level Devices

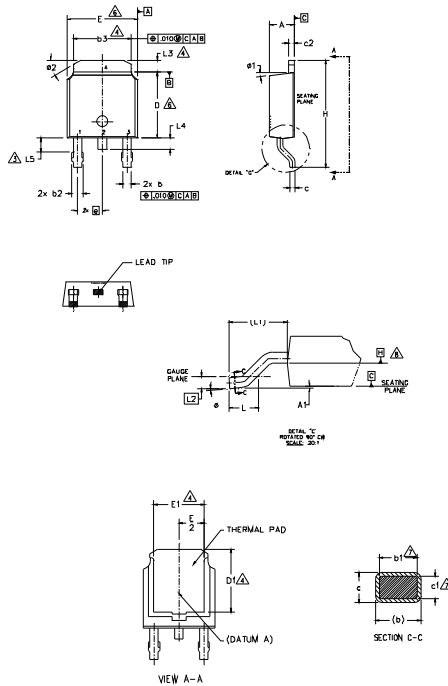
Fig 16. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET[®] Power MOSFETs

IRFR825TRPbF

International
IR Rectifier

D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
- 1- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 - 2- DIMENSIONS ARE SHOWN IN INCHES (MILLIMETERS)
 - 3- LEAD DIMENSION UNCONTROLLED IN L5.
 - 4- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
 - 5- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 (0.13 AND 0.25) FROM THE LEAD TIP.
 - 6- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
 - 7- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
 - 8- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
 - 9- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
A	2.18	2.39	.086	.094	
A1	-	0.13	-	.005	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	7
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.216	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	7
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	6
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	6
E1	4.32	-	.170	-	4
e	2.29 BSC		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 BSC		.108 REF.		
L2	0.51 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	4
L4	-	1.02	-	.040	
L5	1.14	1.52	.045	.060	3
#	0"	10"	0"	10"	
#1	0"	15"	0"	15"	
#2	25"	35"	25"	35"	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBT & CoPAK

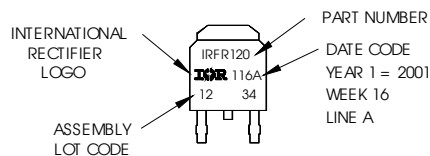
- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120
WITH ASSEMBLY
LOT CODE 1234
ASSEMBLED ON WW 16, 2001
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position
indicates "Lead-Free"

"P" in assembly line position indicates
"Lead-Free" qualification to the consumer-level



OR



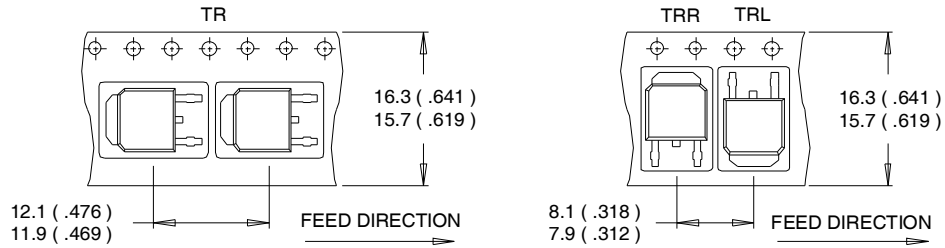
PART NUMBER
DATE CODE
P = DESIGNATES LEAD-FREE
PRODUCT (OPTIONAL)
P̄ = DESIGNATES LEAD-FREE
PRODUCT QUALIFIED TO THE
CONSUMER LEVEL (OPTIONAL)

YEAR 1 = 2001
WEEK 16
A = ASSEMBLY SITE CODE

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

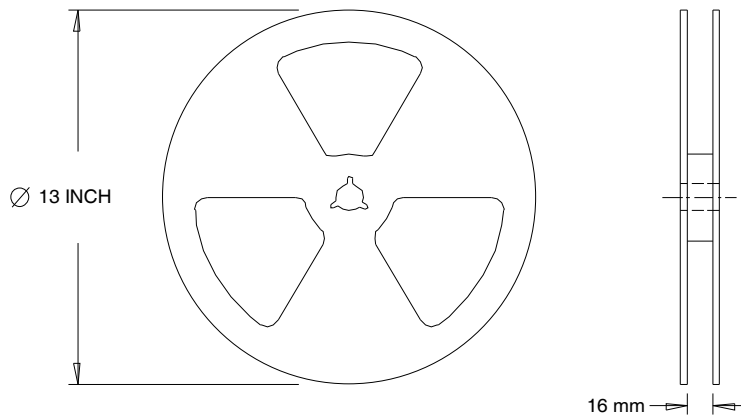
D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

Data and specifications subject to change without notice.
 This product has been designed and qualified for the Industrial market.
 Qualification Standards can be found on IR's Web site.



Стандарт Электрон Связь

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

Наши контакты:

Телефон: +7 812 627 14 35

Электронная почта: sales@st-electron.ru

Адрес: 198099, Санкт-Петербург,
Промышленная ул, дом № 19, литера Н,
помещение 100-Н Офис 331